

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1358

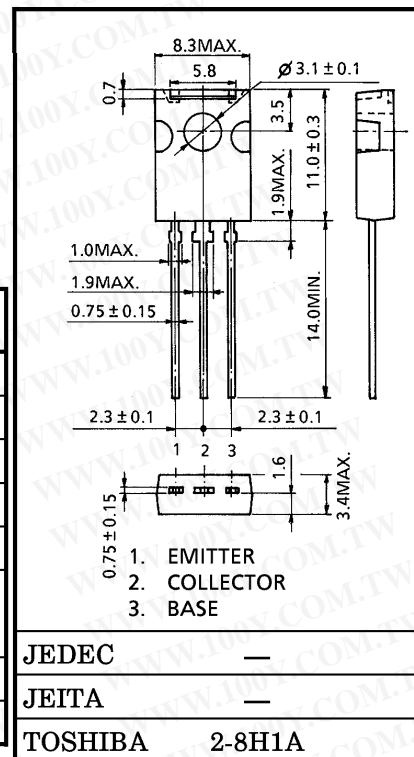
AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS

- Complementary to 2SC3421
- Suitable for Driver of 60 to 80 Watts.
- High Breakdown Voltage.

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-120	V
Collector-Emitter Voltage	V _{CEO}	-120	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-1	A
Base Current	I _B	-100	mA
Collector Power Dissipation	P _C	T _a = 25°C	1.5
		T _c = 25°C	10
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

Unit in mm



Weight : 0.82g (Typ.)

ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = -120V, I _E = 0	—	—	-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C = 0	—	—	-100	nA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = -10mA, I _B = 0	-120	—	—	V
Emitter-Base Breakdown Voltage	V (BR) EBO	I _E = -1mA, I _C = 0	-5	—	—	V
DC Current Gain	h _{FE} (Note)	V _{CE} = -5V, I _C = -100mA	80	—	240	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -500mA, I _B = -50mA	—	-0.40	-1.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -5V, I _C = -500mA	—	-0.77	-1.0	V
Transition Frequency	f _T	V _{CE} = -5V, I _C = -100mA	—	120	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	30	—	pF

(Note) : h_{FE} Classification O : 80~160, Y : 120~240

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